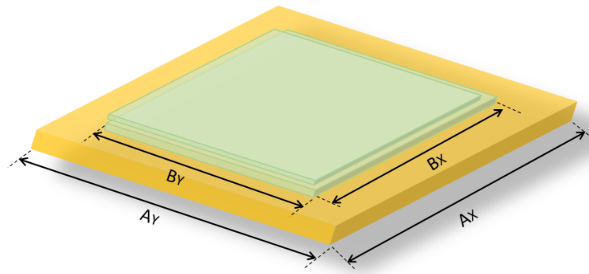


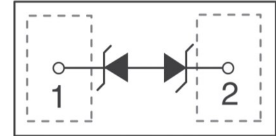


| Mechanical Data | Notes |
|---|---|
| Dice size | Ax:380um,Ay:430um,Bx:180um,By:230um |
| Wafer size | 4” |
| Chip Thickness | 138um±12um |
| Scribe line width | 60um |
| Top metal | Al for wire bonding,d=2.2um±0.2um |
| Back side metal | Ti-Ni-Ag for soldering |

| Parameter | Symbol | Conditions | Value | Unit |
|---|---|---|---|---|
| Reverse stand-off voltage | VRWM | | 5.0 | V |
| Peak pulse power | PPP | Tp=8/20us | 130 | W |
| Peak pulse current | IPP | Tp=8/20us | 12.0 | A |
| Electrostatic discharge | VESD | IEC61000-4-2 Level 4 | ± 15(AIR) | KV |
| Max.junction temp. | Tj | | +150 | ℃ |

Characteristics TA=25℃

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|---|---|---|---|---|---|---|
| Breakdown Voltage | VBR | IT=1mA | 5.6 | | 9.4 | V |
| Reverse leakage current | IR | VR=5V | | | 0.09 | uA |
| Clamping voltage | VC | IPP=1.0A<br>IPP=12A | | | 10.0<br>14.0 | V |
| Diode capacitancd pin1 to 2 | Cj | VR=0V<br>f=1MHz | | 24.0 | 30.0 | pf |

Notes:

(1)sampling testing:no bad dice inking/guaranteed good die >93%

(2)Testing follow customer

(3)Tj=Ta+Rth(j-a)*(pf+pr),where Rth(j-a)-thermal resistance,Pf-forward power dissipation,
Pr-revers power dissipation

(4)**For device testing